

Device Modeling Report

COMPONENTS:

DIODE/ SCHOOTTKY RECTIFIER / STANDARD

PART NUMBER: HSD226

MANUFACTURER: RENESAS

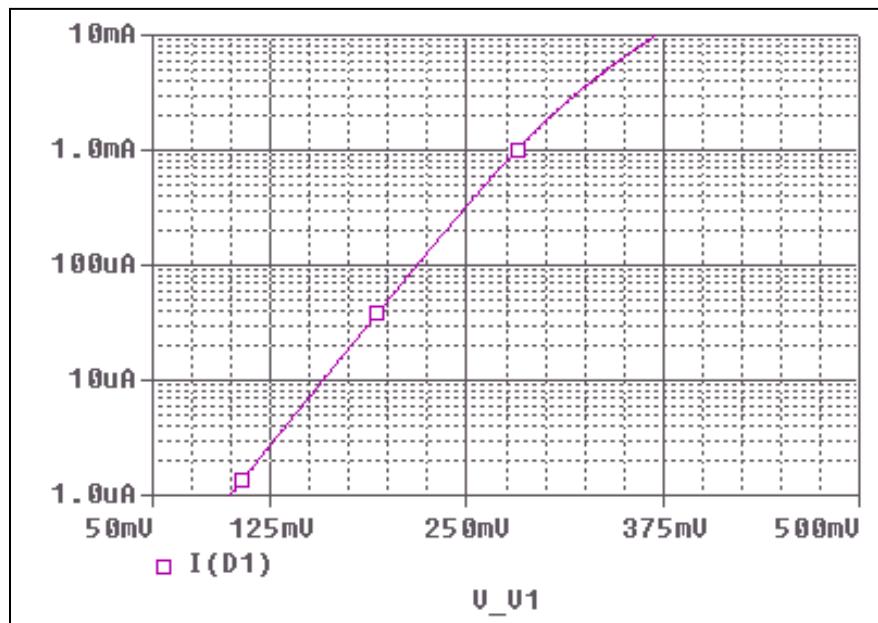


Bee Technologies Inc.

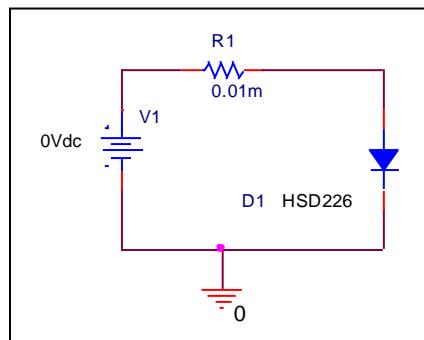
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

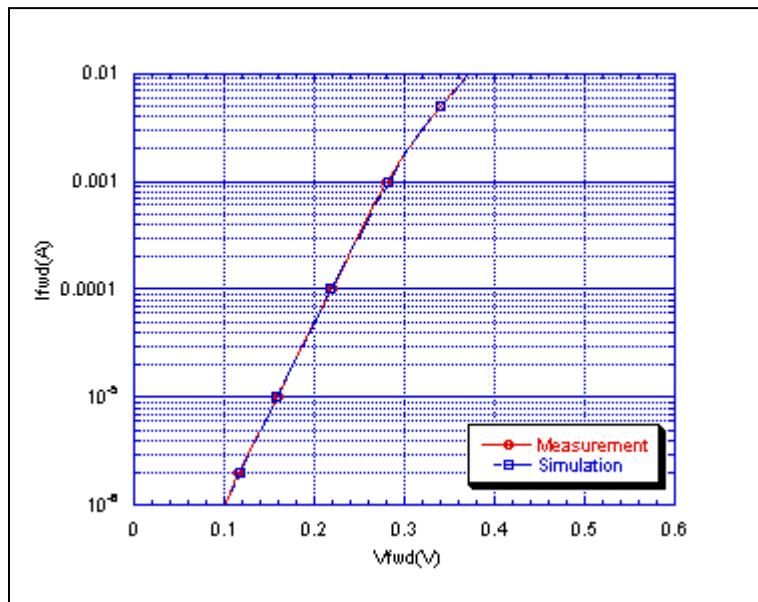


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

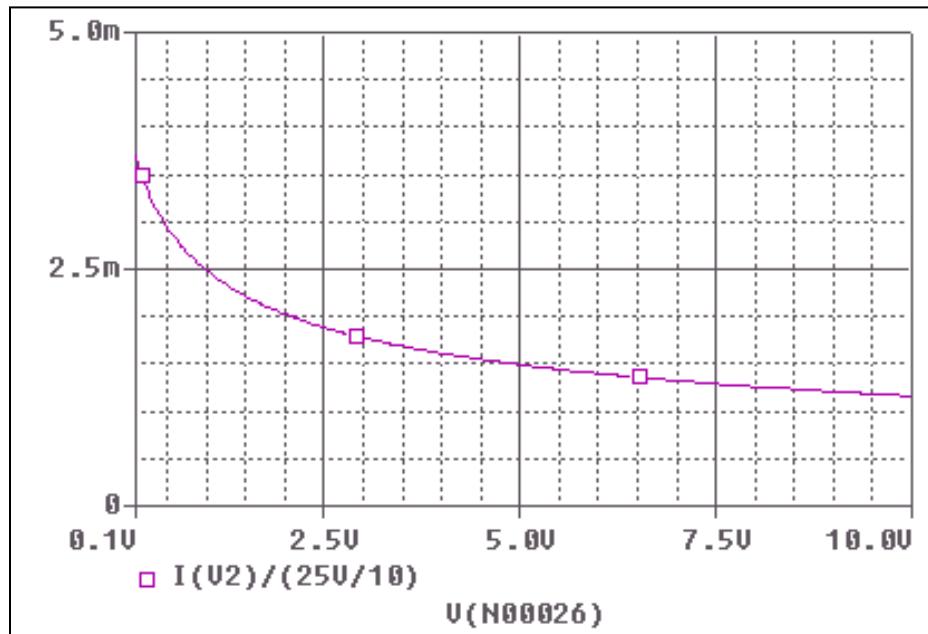


Simulation Result

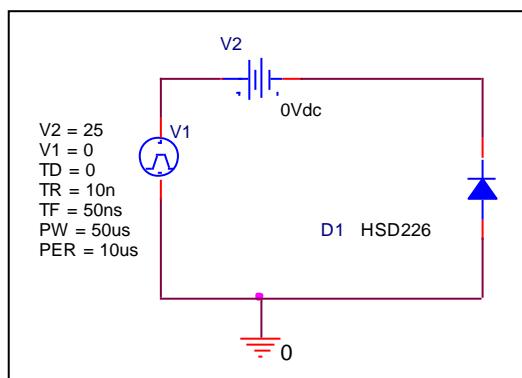
$I_{fwd}(A)$	$V_{fwd}(V)$ Measurement	$V_{fwd}(V)$ Simulation	%Error
1.00E-06	0.100	0.099	-0.80
1.00E-05	0.160	0.158	-1.06
0.0001	0.220	0.218	-0.82
0.0002	0.238	0.237	-0.63
0.0005	0.260	0.262	0.62
0.001	0.280	0.282	0.61
0.002	0.305	0.304	-0.36
0.005	0.340	0.339	-0.29
0.01	0.370	0.371	0.19

Junction Capacitance Characteristic

Circuit Simulation Result

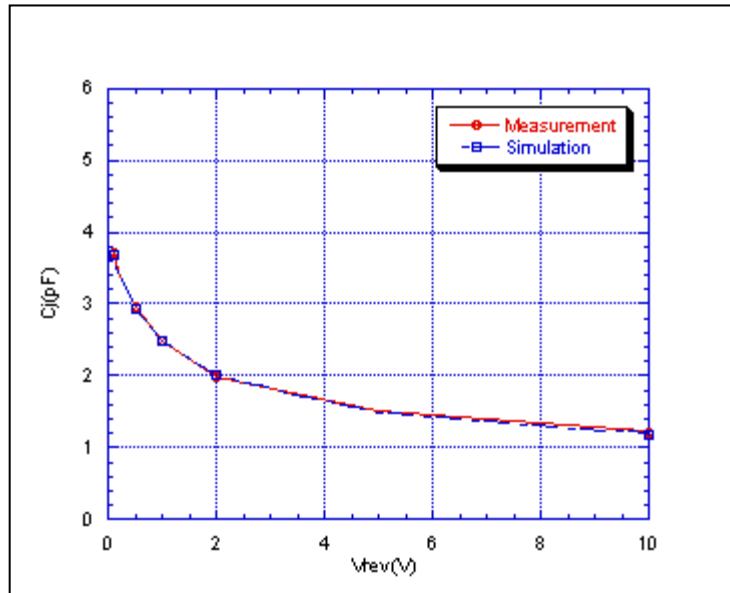


Evaluation Circuit



Comparison Graph

Circuit Simulation Result



Simulation Result

$V_{rev}(V)$	$C_j(pF)$ Measurement	$C_j(pF)$ Simulation	%Error
0.1	3.710	3.690	-0.54
0.2	3.450	3.440	-0.29
0.5	2.950	2.940	-0.34
1	2.480	2.490	0.40
2	1.980	2.020	2.02
5	1.500	1.490	-0.67
10	1.200	1.170	-2.50